

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: **Hiroji EBE, et al.**

Serial Number: **Not Yet Assigned**

Filed: **September 16, 2003**

For: **QUANTUM OPTICAL SEMICONDUCTOR DEVICE**

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

September 16, 2003

Sir:

In compliance with 37 CFR 1.56, Applicants call to the attention of the Patent and Trademark

Office the references listed on the attached PTO-1449.

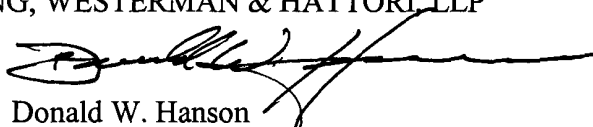
A copy of each of the references are enclosed herewith.

In the event there are any fees due in connection with the filing of this paper, please charge

Deposit Account No. 01-2340.

Respectfully submitted,

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PATENT TRADEMARK OFFICE

Enclosures: PTO-1449; References (4)

INFORMATION DISCLOSURE STATEMENT PTO-1449	Atty. Docket No. 031171	Serial No. New Application
	Applicant(s): Hiroji EBE, et al.	
	Filing Date: September 16, 2003	Group Art Unit: Not Yet Assigned

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA					
_____	AB					
_____	AC					
_____	AD					

FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)	
_____	AE	9-326506	12/16/97	Japan	Yes-Abstract/Discussed in the specification
_____	AF				

OTHER DOCUMENTS

_____	AG	D. Leonard et al.; "Direct formation of quantum-sized dots from uniform coherent islands of InGaAs on GaAs surfaces"; <i>Applied Physics Letters</i> ; Vol. 63; No. 23; December 6 1993; pp. 3203-3205./Discussed in the specification.		
_____	AH	K. Mukai et al.; "Self-Formed In _{0.5} Ga _{0.5} As Quantum Dots on GaAs Substrates Emitting at 1.3μm"; <i>Japanese Journal of Applied Physics</i> Vol. 33; Part 2, No. 12A; December 1 1994; pp. L1710-1712./Discussed in the specification.		
_____	AI	J. Oshinowo et al.; "Highly uniform InGaAs/GaAs quantum dots (~15 nm) by metalorganic chemical vapor deposition"; <i>Applied Physics Letters</i> ; Vol. 65; No. 11; September 12 1994; pp. 1421-1423./Discussed in the specification.		
<table border="1" style="width: 100%;"> <tr> <td style="width: 50%;">Examiner</td> <td style="width: 50%;">Date Considered</td> </tr> </table>			Examiner	Date Considered
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